

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2815	257/296.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/28 09:16
L2	562	257/302.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/28 09:23
L3	1046	257/301.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/28 09:23
L4	1	(vertical adj transistor\$1) AND substrate AND row\$1 AND (x near direction) AND column AND (y near direction) AND perpendicular AND trench\$2 AND isolat\$3 AND (active near region\$1) AND cell\$1 AND (charge near carrier) AND ((bottom lower) near (source drain)) AND ((top upper) near (source drain)) AND channel\$1 AND (gate near electrode) AND (gate near (oxide dielectric insulat\$3)) AND (layer near bod\$3).CLM.	US-PGPUB; USPAT	OR	ON	2006/04/28 09:30